B1 cont'd benefit of priority from U.S. provisional application 60/063,010, titled Low Temperature Method for Forming a Thin, Uniform Oxide, filed 10/23/97.--.

Page 1, lines 23 and 24, please replace "thin oxides with high thickness uniformly" with --thin, uniform oxides--

IN THE CLAIMS:

Please add claims 23 - 25 as shown below.

23. (new) The method of Claim 1, wherein the gate oxide film has a voltage breakdown resistance greater than about 10 MV/cm.

B2 24. (new) The method of Claim 18, wherein the gate oxide film has a voltage breakdown resistance greater than about 10 MV/cm.

25. (new) The method of Claim 18, wherein the gate oxide film has a voltage breakdown resistance of at least 12 MV/cm.

REMARKS

Claims 1 - 22 were pending in the present application and have been rejected by Examiner. This reply adds claims 23 - 25. Applicants respectfully request reconsideration of the rejection in light of the amendments.

1. Applicants did not cancel the ozone generator material because Applicants believe that it is part of the original disclosure. Lines 5 and 6 of Applicants' declaration refer to both the specification "and the preliminary amendment dated September 28, 1998." The ozone generator material was part of the amendment dated September 28, 1998.

2. The Office Action rejected claim 18 under 35 U.S.C. § 103 as being unpatentable over Fujishiro *et al.* (Fujishiro '571) in combination with Nayar *et al.* (Nayar article). Claim 18's limitations include "exposing the silicon surface to an atmosphere including ozone, while maintaining the substrate at the first temperature, wherein the exposing step creates a first, **uniformly thick**, gate oxide film".